

P-Channel 30 V (D-S) MOSFET

PowerPAK® SC-70-6L Single


Marking code: KA

| PRODUCT SUMMARY | |
|-----------------------------------------------------|--------|
| V_{DS} (V) | -30 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = -10$ V | 0.020 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V | 0.033 |
| Q_g typ. (nC) | 8.3 |
| I_D (A) ^f | -12 |
| Configuration | Single |

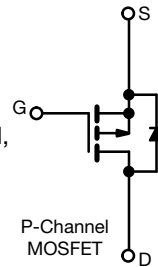
FEATURES

- TrenchFET® Gen IV p-channel power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
- Provides excellent R_{DS-Q_g} Figure-of-Merit (FOM) for switching applications
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- Battery charging and management
- Load switch
- DC/DC converters
- Power management in battery-operated, mobile and wearable devices



| ORDERING INFORMATION | |
|---------------------------------|------------------|
| Package | PowerPAK SC-70 |
| Lead (Pb)-free and halogen-free | SiA483ADJ-T1-GE3 |

| ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted) | | | |
|-------------------------------------------------------------------|----------------|---------------|-----------------------|
| PARAMETER | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | V_{DS} | -30 | V |
| Gate-source voltage | V_{GS} | -20 / +16 | |
| Continuous drain current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | -12 ^f |
| | | $T_C = 70$ °C | -12 ^f |
| | | $T_A = 25$ °C | -10.6 ^{a, b} |
| | | $T_A = 70$ °C | -8.5 ^{a, b} |
| Pulsed drain current ($t = 100$ μ s) | I_{DM} | -60 | A |
| Continuous source-drain diode current | I_S | $T_C = 25$ °C | |
| | | $T_A = 25$ °C | -2.9 ^{a, b} |
| Maximum power dissipation | P_D | $T_C = 25$ °C | 17.9 |
| | | $T_C = 70$ °C | 11.4 |
| | | $T_A = 25$ °C | 3.4 ^{a, b} |
| | | $T_A = 70$ °C | 2.2 ^{a, b} |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +150 | °C |
| Soldering recommendations (peak temperature) ^{c, d} | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | | |
|---------------------------------------------|--------------|------------|---------|---------|------|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT |
| Maximum junction-to-ambient ^{a, e} | $t \leq 5$ s | R_{thJA} | 29 | 37 | °C/W |
| Maximum junction-to-case (drain) | Steady state | R_{thJC} | 5.5 | 7 | |

Notes

- Surface mounted on 1" x 1" FR4 board
- $t = 5$ s
- See solder profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 80 °C/W
- Package limited



| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|-----------------------------------------------------------------------------|-------------------------|------------------------------------------------------------------------------------------------------------------------------------------|------|-------|-----------|----------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$ | -30 | - | - | V |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | $I_D = -250\text{ }\mu\text{A}$ | - | -26 | - | mV/ $^\circ\text{C}$ |
| $V_{GS(th)}$ temperature coefficient | $\Delta V_{GS(th)}/T_J$ | | - | 5 | - | |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$ | -1 | - | -2.5 | V |
| Gate-source leakage | I_{GSS} | $V_{DS} = 0\text{ V}$, $V_{GS} = -20\text{ V} / +16\text{ V}$ | - | - | ± 100 | nA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$ | - | - | -1 | μA |
| | | $V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^\circ\text{C}$ | - | - | -10 | |
| On-state drain current ^a | $I_{D(on)}$ | $V_{DS} \leq -5\text{ V}$, $V_{GS} = 0\text{ V}$ | -10 | - | - | A |
| Drain-source on-state resistance ^a | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}$, $I_D = -5\text{ A}$ | - | 0.016 | 0.020 | Ω |
| | | $V_{GS} = -4.5\text{ V}$, $I_D = -3\text{ A}$ | - | 0.025 | 0.033 | |
| Forward transconductance ^a | g_{fs} | $V_{DS} = -10\text{ V}$, $I_D = -5\text{ A}$ | - | 25 | - | S |
| Dynamic ^b | | | | | | |
| Input capacitance | C_{ISS} | $V_{DS} = -15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$ | - | 950 | - | pF |
| Output capacitance | C_{OSS} | | - | 460 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 50 | - | |
| Total gate charge | Q_g | $V_{DS} = -15\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -10.6\text{ A}$ | - | 17 | 26 | nC |
| | | $V_{DS} = -15\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -10.6\text{ A}$ | - | 8.3 | 12.5 | |
| Gate-source charge | Q_{gs} | $V_{DS} = -15\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -10.6\text{ A}$ | - | 3.7 | - | nC |
| Gate-drain charge | Q_{gd} | | - | 3 | - | |
| Gate resistance | R_g | $f = 1\text{ MHz}$ | 1.5 | 8.8 | 15 | Ω |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = -15\text{ V}$, $R_L = 1.8\text{ }\Omega$, $I_D \cong -8.5\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 1\text{ }\Omega$ | - | 26 | 52 | ns |
| Rise time | t_r | | - | 95 | 190 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 24 | 80 | |
| Fall time | t_f | | - | 16 | 32 | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = -15\text{ V}$, $R_L = 1.8\text{ }\Omega$, $I_D \cong -8.5\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\text{ }\Omega$ | - | 12 | 24 | |
| Rise time | t_r | | - | 6 | 12 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 30 | 60 | |
| Fall time | t_f | | - | 8 | 16 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous source-drain diode current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | - | - | -12 | A |
| Pulse diode forward current | I_{SM} | | - | - | -60 | |
| Body diode voltage | V_{SD} | $I_S = -10\text{ A}$, $V_{GS} = 0\text{ V}$ | - | -0.85 | -1.2 | V |
| Body diode reverse recovery time | t_{rr} | $I_F = -8.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$ | - | 19 | 38 | ns |
| Body diode reverse recovery charge | Q_{rr} | | - | 7 | 14 | nC |
| Reverse recovery fall time | t_a | | - | 9 | - | ns |
| Reverse recovery rise time | t_b | | - | 10 | - | |

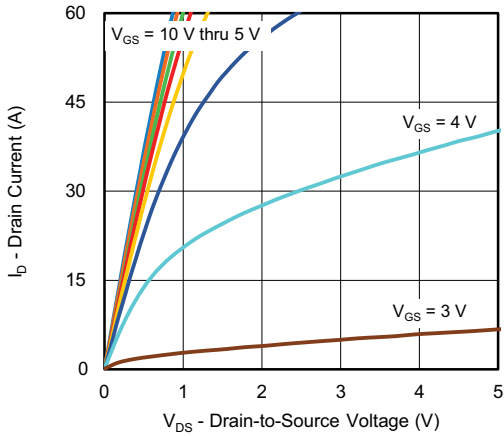
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

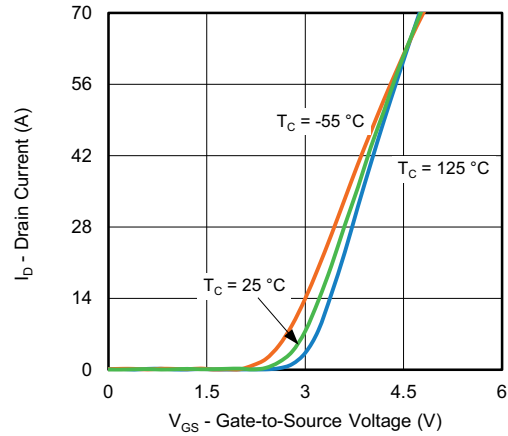
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



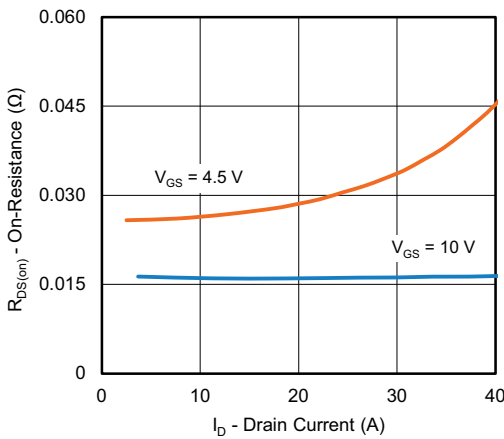
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



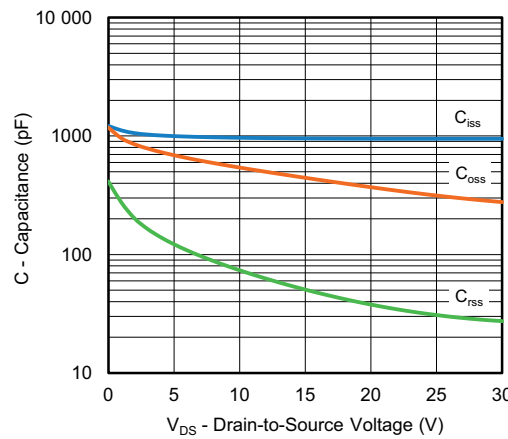
Output Characteristics



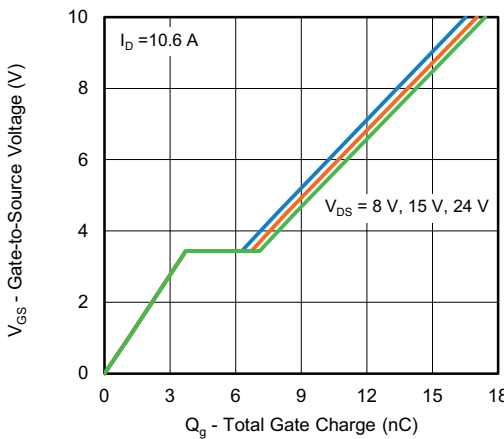
Transfer Characteristics



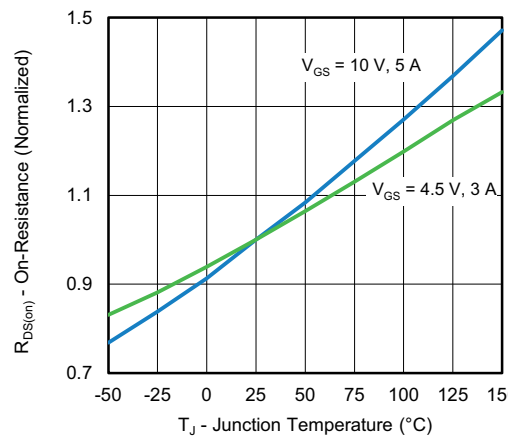
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

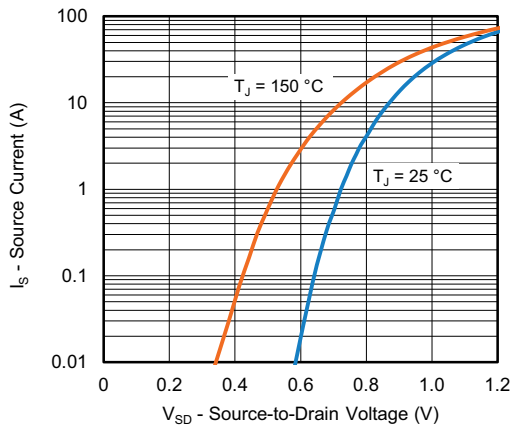


Gate Charge

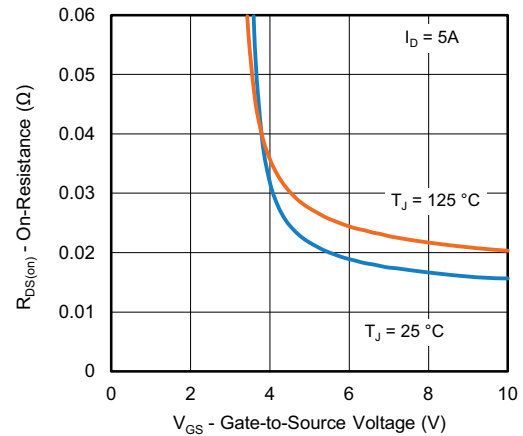


On-Resistance vs. Junction Temperature

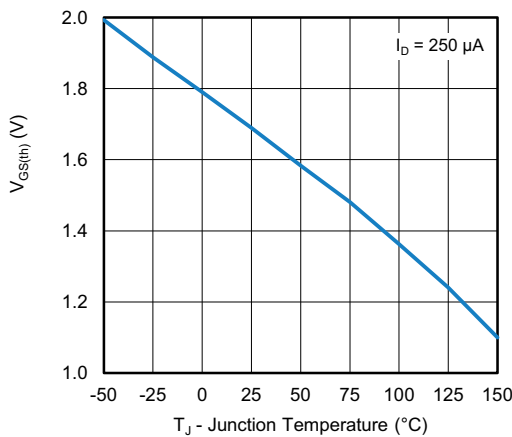
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



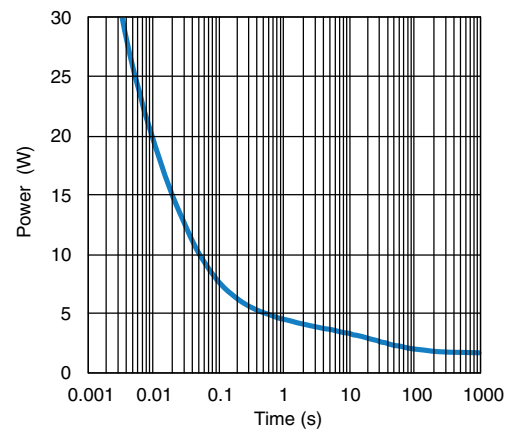
Source-Drain Diode Forward Voltage



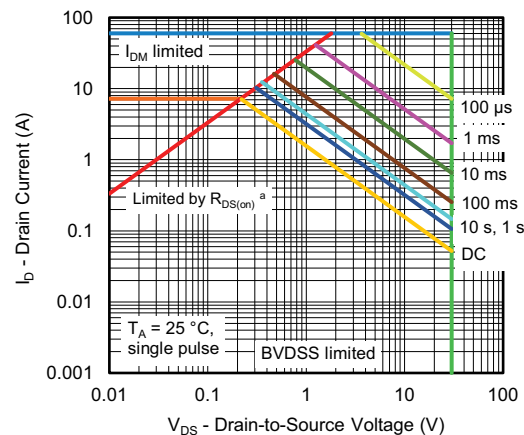
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



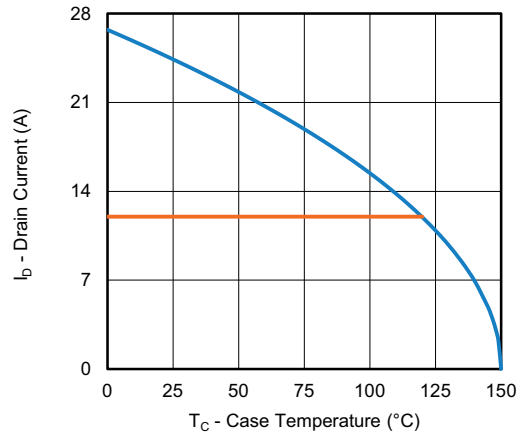
Safe Operating Area, Junction-to-Ambient

Note

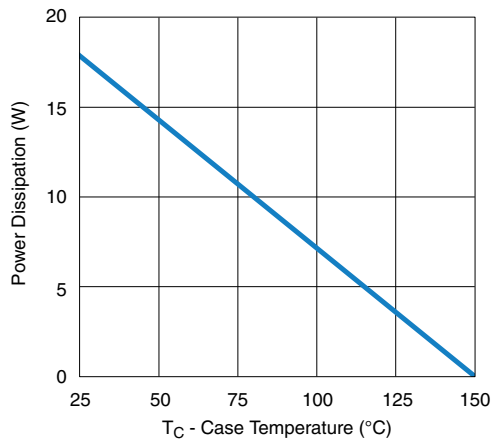
a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



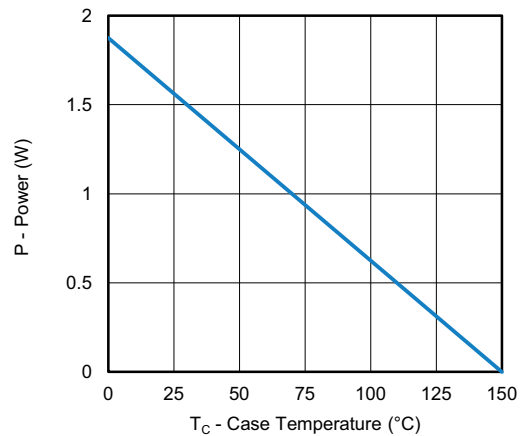
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Power, Junction-to-Case



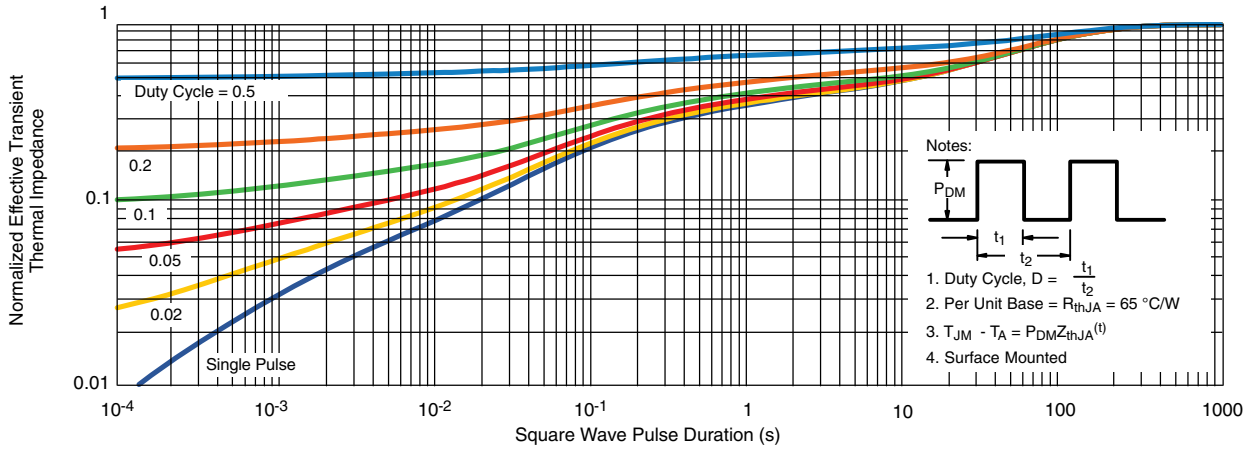
Power, Junction-to-Ambient

Note

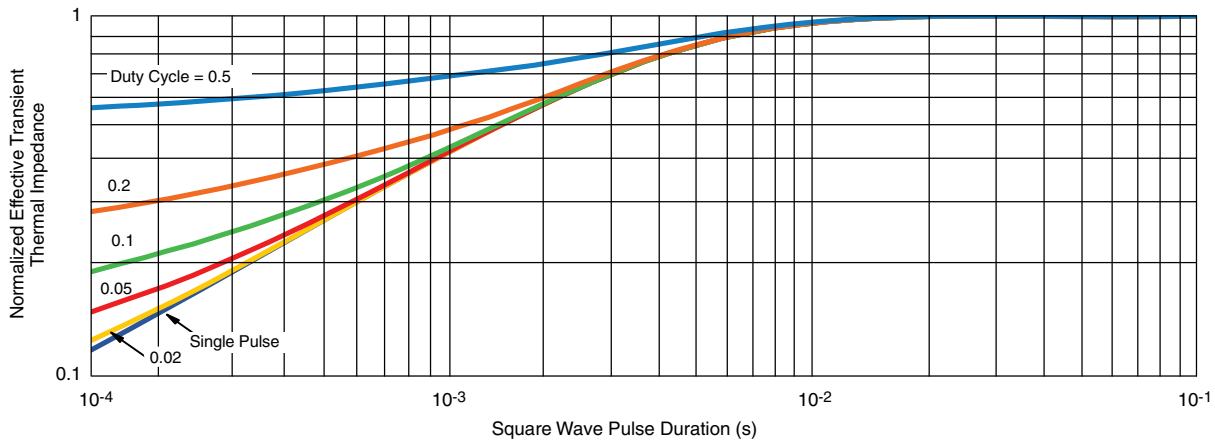
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® SC70-6L



BACKSIDE VIEW OF SINGLE



BACKSIDE VIEW OF DUAL



- Notes:
 1. All dimensions are in millimeters
 2. Package outline exclusive of mold flash and metal burr
 3. Package outline inclusive of plating

| DIM | SINGLE PAD | | | | | | DUAL PAD | | | | | |
|-----|-------------|-------|-------|-----------|-------|-------|-------------|-------|-------|-----------|-------|-------|
| | MILLIMETERS | | | INCHES | | | MILLIMETERS | | | INCHES | | |
| | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max |
| A | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 |
| A1 | 0 | - | 0.05 | 0 | - | 0.002 | 0 | - | 0.05 | 0 | - | 0.002 |
| b | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 |
| C | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| D | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 |
| D1 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | 0.513 | 0.613 | 0.713 | 0.020 | 0.024 | 0.028 |
| D2 | 0.135 | 0.235 | 0.335 | 0.005 | 0.009 | 0.013 | | | | | | |
| E | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 |
| E1 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 |
| E2 | 0.345 | 0.395 | 0.445 | 0.014 | 0.016 | 0.018 | | | | | | |
| E3 | 0.425 | 0.475 | 0.525 | 0.017 | 0.019 | 0.021 | | | | | | |
| e | 0.65 BSC | | | 0.026 BSC | | | 0.65 BSC | | | 0.026 BSC | | |
| K | 0.275 TYP | | | 0.011 TYP | | | 0.275 TYP | | | 0.011 TYP | | |
| K1 | 0.400 TYP | | | 0.016 TYP | | | 0.320 TYP | | | 0.013 TYP | | |
| K2 | 0.240 TYP | | | 0.009 TYP | | | 0.252 TYP | | | 0.010 TYP | | |
| K3 | 0.225 TYP | | | 0.009 TYP | | | | | | | | |
| K4 | 0.355 TYP | | | 0.014 TYP | | | | | | | | |
| L | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 |
| T | | | | | | | 0.05 | 0.10 | 0.15 | 0.002 | 0.004 | 0.006 |

ECN: C-07431 – Rev. C, 06-Aug-07
 DWG: 5934

RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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